

L Number	Hits	Search Text	DB	Time stamp
1	24	((liquid adj crystal)and (contact adj hole)and (gate adj pad adj electrode)	USPAT; US-PGPUB; JPO	2004/03/31 13:37
49	165	((gate adj pad) with insulat\$4) and 349/\$.ccls.	USPAT; US-PGPUB; JPO	2004/03/31 15:55
-	1655	349/139	USPAT; JPO	2003/10/03 14:56
-	1048	349/138	USPAT; JPO	2002/07/30 09:30
-	218	349/147	USPAT; JPO	2002/07/30 09:30
-	902	349/113	USPAT; JPO	2002/07/30 09:30
-	137	349/47	USPAT; JPO	2002/07/30 09:31
-	4950	((contact adj hole) with silicon)	USPAT; JPO	2002/07/30 09:34
-	100	((contact adj hole) with silicon) and 349/\$.ccls.	USPAT; JPO	2004/03/31 15:55
-	317	((contact adj hole) with silicon) and (349/\$.ccls or (liquid adj crystal))	USPAT; JPO	2002/07/30 09:35
-	239	((contact adj hole) with silicon) and (349/\$.ccls or (liquid adj crystal))and expos\$4	USPAT; JPO	2002/07/30 09:37
-	234	((contact adj hole) with silicon) and (349/\$.ccls or (liquid adj crystal))and expos\$4 and (passivation or insulat\$4)	USPAT; JPO	2002/09/30 17:05
-	31	((contact adj hole) with silicon) and (349/\$.ccls or (liquid adj crystal))and expos\$4 and (passivation or insulat\$4) and 349/139	USPAT; JPO	2003/10/03 14:57
-	59	349/139 and 349/113	USPAT; JPO	2002/07/30 17:56
-	63	349/138 and 349/113	USPAT; JPO	2002/07/30 18:00
-	24	349/147 and 349/113	USPAT; JPO	2002/07/30 18:02
-	9	349/47 and 349/113	USPAT; JPO	2002/07/30 18:03
-	636	((contact adj hole) and silicon) and 349/\$.ccls.	USPAT; JPO	2002/09/30 09:04
-	631	((contact adj hole) and silicon) and 349/\$.ccls. and insulat\$4	USPAT; JPO	2002/09/30 09:04
-	162	((contact adj hole) same silicon) and 349/\$.ccls. and (insulat\$4 same expos\$4)	USPAT; JPO	2003/01/21 08:50
-	188	349/139 and(contact adj hole)	USPAT; JPO	2002/09/30 17:07
-	139	349/139 and((contact adj hole) same (pixel or pad))	USPAT; JPO	2003/01/21 08:47
-	9	6163356.pn. or 6190934.pn. or 5920083.pn. or 6300152.pn. or 6188461.pn. or 6078366.pn. or 5784131.pn. or 6310669.pn. or 6424399.pn.	USPAT	2003/01/20 17:19
-	1	6344884.pn.	USPAT	2003/01/20 17:19
-	174	((contact adj hole) same pad) and 349/\$.ccls. and expos\$4	USPAT; US-PGPUB; JPO	2003/01/21 08:58
-	224	349/139 and((contact adj hole) same (pixel or pad))	USPAT; US-PGPUB; JPO	2003/01/21 10:08
-	3	5235443.pn. or 5295009.pn. or 5309265.pn.	USPAT; JPO	2003/01/22 10:34
-	773	438/30	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 13:59
-	348	438/30 and (contact adj hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:05
-	114	Qi.xa.	USPAT	2003/04/14 16:56
-	5386	sung.in.	USPAT; US-PGPUB	2003/04/14 16:57
-	396	sung.in. and (liquid adj crystal)	USPAT; US-PGPUB	2003/04/14 16:57
-	105	sung.in. and (liquid adj crystal)and (contact adj hole)	USPAT; US-PGPUB	2003/04/14 17:47
-	4656	(liquid adj crystal)and (contact adj hole)	USPAT; US-PGPUB	2004/02/09 12:55

-	466	349/152	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/03 14:57
-	13	((contact adj hole) with silicon) and (349/\$.cc1s or (liquid adj crystal))and expos\$4 and (passivation or insulat\$4) and 349/152	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/03 14:57
-	1	20010030718.pn.	USPAT; US-PGPUB	2004/02/09 10:05
-	23	(liquid adj crystal)and (contact adj hole)and (gate adj pad adj electrode)	USPAT; US-PGPUB; JPO	2004/03/31 13:37